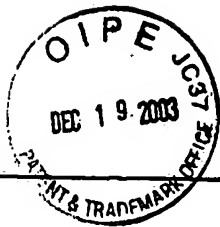


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<b>INFORMATION DISCLOSURE STATEMENT</b>				<b>APPLICANT(S): Wu et al.</b>			
				<b>SERIAL NO.: 10/603,852</b>			
				<b>FILING DATE: June 25, 2003</b>		<b>GROUP: 2811</b>	
<b>U.S. PATENT DOCUMENTS</b>							
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<i>210</i>	A1	4,010,045	03/01/1977	Ruehrwein			
	A2	5,013,681	05/07/1991	Godbey et al.			
	A3	5,166,084	11/24/1992	Pfiester			
	A4	5,202,284	04/13/1993	Kamins et al.			
	A5	5,207,864	05/04/1993	Bhat et al.			
	A6	5,208,182	05/04/1993	Narayan et al.			
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	A19	5,523,592	06/04/1996	Nakagawa et al.			
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	A22	5,540,785	07/30/1996	Dennard et al.			
	A23	5,683,934	11/04/1997	Candelaria			
<i>210</i>	A24	5,728,623	03/17/1998	Mori			
<b>EXAMINER</b> <i>Doug L. O.</i>				<b>DATE CONSIDERED</b> <i>5/21/04</i>			



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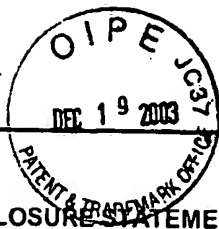
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	A26	5,792,679	08/11/1998	Nakato			
	A27	5,877,070	03/02/1999	Goesele et al.			
	A28	5,891,769	04/06/1999	Liaw et al.			
	A29	5,906,708	05/25/1999	Robinson et al.			
	A30	5,906,951	05/25/1999	Chu et al.			
	A31	5,943,560	08/24/1999	Chang et al.			
	A32	5,966,622	10/12/1999	Levine et al.			
	A33	5,998,807	12/07/1999	Lustig et al.			
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	A42	6,117,750	09/12/2000	Bensahel et al.			
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EXAMINER <i>Donna L. Owen</i>				DATE CONSIDERED <i>5/21/04</i>			



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QK0	A50	6,207,977	03/27/2001	Augusto			
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	A52	6,218,677 B1	04/17/2001	Broekaert			
	A53	6,232,138 B1	05/15/2001	Fitzgerald et al.			
	A54	6,235,567 B1	05/22/2001	Huang			
	A55	6,251,755 B1	06/26/2001	Furukawa et al.			
	A56	6,261,929 B1	07/17/2001	Gehrke et al.			
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	A65	6,573,126	06/03/2003	Cheng et al.			
	A66	6,583,015	06/24/2003	Fitzgerald et al.			
	A67	2001/0003269 A1	06/14/2001	Wu et al.			
	A68	2002/0125497	09/12/2002	Fitzgerald			
QK0	A69	2003/0013323	01/16/2003	Hammond et al.			

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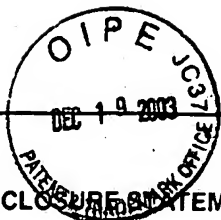
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QK0	B2	0 683 522 A2	11/22/1995	EP				No	Yes

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*Douglas H. Owen*

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Qho	B3	O 828 296	03/11/1998	EP				No	Yes
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Qho	B5	WO 98/59365	12/30/1998	PCT				No	Yes
Qho	B6	WO 99/53539	10/21/1999	PCT				No	Yes
Qho	B7	WO 00/48239	08/17/2000	PCT				No	Yes
Qho	B8	WO 01/99169	12/27/2001	PCT				No	Yes

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Qho	C2	Barradas et al., "RBS analysis of MBE-grown SiGe/(001) Si heterostructures with thin, high Ge content SiGe channels for HMOS transistors," <u>Modern Physics Letters B</u> , (2001), abstract.
Qho	C3	Borenstein et al., "A New Ultra-Hard Etch-Stop Layer for High Precision Micromachining," <u>Proceedings of the 1999 12<sup>th</sup> IEEE International Conference on Micro Electro Mechanical Systems (MEMS)</u> , January 17-21, 1999, pps. 205-210.
Qho	C4	Bruel et al., "SMART CUT: A Promising New SOI Material Technology," <u>Proceedings of the 1995 IEEE International SOI Conference</u> (October 1995), pp. 178-179.
Qho	C5	Bruel, "Silicon on Insulator Material Technology," <u>Electronic Letters</u> , Vol. 13, No. 14 (July 6, 1995), pp. 1201-1202.
Qho	C6	Brunner et al., "Molecular beam epitaxy growth and thermal stability of Si <sub>1-x</sub> Ge <sub>x</sub> layers on extremely thin silicon-on-insulator substrates," <u>Thin Solid Films</u> , Vol. 321 (1998), pp. 245-250.
Qho	C7	Chang et al., "Selective Etching of SiGe/Si Heterostructures," <u>Journal of the Electrochemical Society</u> , No. 1 (January 1991), pp. 202-204.
Qho	C8	Chen et al., "The Band Model and the Etching Mechanism of Silicon in Aqueous KOH," <u>Journal of the Electrochemical Society</u> , Vol. 142, No. 1 (January 1995), pp. 170-176.

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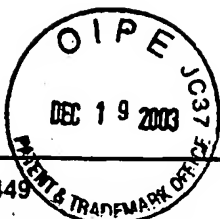
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Wro	C9	Cheng et al., "Electron Mobility Enhancement in Strained-Si n-MOSFETs Fabricated on SiGe-on-Insulator (SGOI) Substrates," <u>IEEE Electron Device Letters</u> , Vol. 22, No. 7 (July 2001), pp. 321-323.	
	C10	Cheng et al., "Relaxed Silicon-Germanium on Insulator Substrate by Layer Transfer," <u>Journal of Electronic Materials</u> , Vol. 30, No. 12 (2001), pp. L37-L39.	
	C11	Feijoo et al., "Epitaxial Si-Ge Etch Stop Layers with Ethylene Diamine Pyrocatechol for Bonded and Etchback Silicon-on-Insulator," <u>Journal of Electronic Materials</u> , Vol. 23, No. 6 (June 1994), pps. 493-496.	
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	C17	Hackbarth et al., "Alternatives to thick MBE-grown relaxed SiGe buffers," <u>Thin Solid Films</u> , Vol. 369, No. 1-2 (July 2000), pp. 148-151.	
	C18	Huang et al., "High-quality strain-relaxed SiGe alloy grown on implanted silicon-on-insulator substrate," <u>Applied Physics Letters</u> , Vol. 76, No. 19 (May 8, 2000), pp. 2680-2682.	
	C19	Ishikawa et al., "Creation of Si-Ge-based SIMOX structures by low energy oxygen implantation," <u>Proceedings of the 1997 IEEE International SOI Conference</u> (October 1997), pp. 16-17.	
	C20	Ishikawa et al., "SiGe-on-insulator substrate using SiGe alloy grown Si(001)," <u>Applied Physics Letters</u> , Vol. 75, No. 7 (August 16, 1999), pp. 983-985.	
	C21	Ismail, "Si/SiGe High-Speed Field-Effect Transistors," Electron Devices Meeting, Washington D.C., December 10, 1995.	
	C22	König et al., "Design Rules for n-Type SiGe Hetero FETs," <u>Solid State Electronics</u> , Vol. 41, No. 10 (1997), pp. 1541-1547.	
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	C25	Leitz et al., "Dislocation glide and blocking kinetics in compositionally graded SiGe/Si," <u>Journal of Applied Physics</u> , Vol. 90, No. 6 (September 15, 2001), pp. 2730-2736.	
	C26	Maiti et al., "Strained-Si heterostructure field effect transistors," <u>Semiconductor Science and Technology</u> , Vol. 13 (1998), pp. 1225-1246.	
	C27	Mazara, "Silicon-On-Insulator by Wafer Bonding: A Review," <u>Journal of the Electrochemical Society</u> , No. 1 (January 1991), pp. 341-347.	
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	C30	Powell et al., "New approach to the growth of low dislocation relaxed SiGe material," <u>Applied Physics Letters</u> , Vol. 64, No. 14 (April 4, 1994), pp. 1865-1858.	
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	C36	Ting et al., "Monolithic Integration of III-V Materials and Devices on Silicon," Part of the SPIE Conference on Silicon-Based Optoelectronics, San Jose, CA, (January 1999), pp. 19-28.	
	C37	Usami et al., "Spectroscopic study of Si-based quantum wells with neighboring confinement structure," <u>Semiconductor Science and Technology</u> , (1997), abstract.	
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EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)		
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I	C40	Yi et al., "Si <sub>1-x</sub> Ge <sub>x</sub> /Si Multiple Quantum Well Wires Fabricated Using Selective Etching," <u>Materials Research Society Symposium Proceedings</u> , Vol. 379 (1995), pp. 91-96.	
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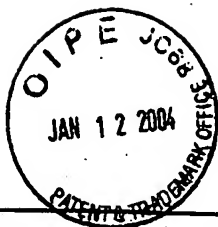
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OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
DWC	C43	Batterman, "Hillocks, Pits, and Etch Rate in Germanium Crystals," <u>Journal of Applied Physics</u> , Vol. 28, No. 11 (November, 1957), pp. 1236-1241.							
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	C47	Feijóo <i>et al.</i> , "Etch Stop Barriers in Silicon Produced by Ion Implantation of Electrically Non-Active Species," <u>Journal of the Electrochemical Society</u> , Vol. 139, No. 8 (August 1992), pp. 2309-2313.							
	C48	Fitzgerald, "GeSi/Si Nanostructures," <u>Annual Review of Materials Science</u> , Vol. 25 (1995), pp. 417-454.							
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	C51	Herzog <i>et al.</i> , "X-Ray Investigation of Boron- and Germanium-Doped Silicon Epitaxial Layers," <u>Journal of the Electrochemical Society</u> , Vol. 131, No. 12 (December 1984), pp.2969-2974.	
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	C53	Hunt <i>et al.</i> , "Selective Etch Stop by Stress Compensation for Thin-Film BESOI," <u>1990 IEEE/SOI Technology Conference</u> , (October 2-4, 1990), pp.145-146.	
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	C55	Kern, "Chemical Etching of Silicon, Germanium, Gallium, Arsenide, and Gallium Phosphide," <u>RCA Review</u> , Vol. 39 (June 1978), pp. 278-308.	
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	C58	Lehmann <i>et al.</i> , "Implanted Carbon: An Effective Etch-Stop in Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 138, No.5 (May 1991), pp. 3-4.	
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	C60	Palik <i>et al.</i> , "Study of Bias-Dependent Etching of Si in Aqueous KOH," <u>Journal of the Electrochemical Society</u> , Vol. 134, No. 2 (February 1987), pp. 404-409.	
	C61	Palik <i>et al.</i> , "Study of the Etch-Stop Mechanism in Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 129, No. 9 (September 1982), pp.2051-2059.	
	C62	Petersen <i>et al.</i> , "Silicon as a Mechanical Material," <u>Proceedings of the IEEE</u> , Vol. 70, No. 5 (May 1982), pp. 420-457.	
D/K	C63	Rai-Choudhury <i>et al.</i> , "Doping of Epitaxial Silicon," <u>Journal of Crystal Growth</u> , Vol. 7 (1970), pp. 361-367.	
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OTHER ART, JOURNAL ARTICLES, ETC.			
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)		
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	C66	Soderberg, "Fabrication of BESOI Materials Using Implanted Nitrogen as an Effective Etch Stop Barrier," <u>1989 IEEE SOS/SOI Technology Conference</u> , (October 3-5, 1989), pp. 64.	
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